IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Withdrawn and Currently Amended): An aqueous dispersion for chemical mechanical polishing comprising abrasive grains, wherein the abrasive grains ~~include~~ comprise:

(A) simple particles composed of at least one selected from the group consisting of inorganic ~~particvles~~ particles and organic particles[[,]]; and

(B) composite particles.

Claim 2 (Withdrawn): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein the simple particles (A) making up the abrasive grains are composed of inorganic particles, and the composite particles (B) are composed of inorganic organic composite particles obtained by integrally combining organic particles with inorganic particles.

Claim 3 (Withdrawn and Currently Amended): The aqueous dispersion for chemical mechanical polishing according to claim 1 or 2, wherein ~~the~~ an overall content of all the abrasive grains is 0.11 to 20% by mass, ~~the~~ a content of the simple particles (A) is 0.1 to 19.99% by mass, and ~~the~~ a content of the composite particles (B) is 0.01 to 19.9% by mass.

Claim 4 (Withdrawn and Currently Amended): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein a value of a specific removal rate ratio (RBM/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the

removal rate (RCu) of a copper film, in the case where the copper film and barrier metal film are polished under the same conditions, is 0.5 to 200.

Claim 5 (Withdrawn and Currently Amended): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein ~~the~~ a value of the specific removal rate ratio (RBM/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the removal rate (RCu) of a copper film, in the case where the copper film and barrier metal film are polished under the same conditions, is 10 to 200.

Claim 6 (Withdrawn and Currently Amended): The aqueous dispersion for chemical mechanical polishing according to claim 1, wherein ~~the~~ a value of the specific removal rate ratio (RBM/RCu) represented by a ratio of the removal rate (RBM) of a barrier metal film to the removal rate (RCu) of a copper film, in the case where the copper film and barrier metal film are polished under the same conditions, is 0.5 to 3.

Claim 7 (Currently Amended): A process for producing a semiconductor device, comprising the step of polishing a surface to be polished of a semiconductor material with ~~the~~ an aqueous dispersion for chemical mechanical polishing ~~according to claim 1~~ comprising abrasive grains,

wherein the abrasive grains comprise:

(A) simple particles comprising at least one selected from the group consisting of inorganic particles and organic particles; and

(B) composite particles, and

wherein the composite particles (B) are composed of inorganic organic composite particles obtained by integrally combining organic particles with inorganic particles.

Claim 8 (Withdrawn): A process for producing a semiconductor device, comprising the first polishing treatment step of mainly polishing a copper film of a surface to be polished of a semiconductor material and the second polishing treatment step of mainly polishing a barrier metal film with the aqueous dispersion for chemical mechanical polishing according to claim 5 or 6, conducted after the first polishing treatment step.

Claim 9 (New): The process for producing a semiconductor device according to claim 7, wherein the inorganic particles have adhered as shell particles to the surfaces of core particles composed of the organic particles.

Claim 10 (New): The process for producing a semiconductor device according to claim 7, wherein the organic particles have adhere as shell particles to surfaces of core particles composed of the inorganic particles.

Claim 11 (New): The process for producing a semiconductor device according to claim 7, wherein the organic particles and inorganic particles have aggregated to each other without forming a clear-shell structure.

Claim 12 (New): The process for producing a semiconductor device according to claim 7, wherein a proportion of the inorganic particles is 1 to 2,000 parts by weight per 100 parts by weight of the organic particles.

Claim 13 (New): The process for producing a semiconductor device according to claim 7, wherein a proportion of the inorganic particles is 10 to 1,000 parts by weight per 100 parts by weight of the organic particles.

Claim 14 (New): The process for producing a semiconductor device according to claim 7, wherein an average particle diameter of the composite particles is 20 to 20,000 nm.

Claim 15 (New): The process for producing a semiconductor device according to claim 7, wherein an average particle diameter of the composite particles is 50 to 5,000 nm.

Claim 16 (New): The process for producing a semiconductor device according to claim 7, wherein an overall content of all the abrasive grains is 0.11 to 20% by mass, a content of the simple particles (A) is 0.1 to 19.99% by mass, and a content of the composite particles (B) is 0.01 to 19.9% by mass.

SUPPORT FOR THE AMENDMENT

Claims 1 and 3-7 are currently amended.

Claims 9-16 are added.

Claims 1 and 3-6 have been amended for minor editorial purposes, and supported by the claims, as originally filed.

Support for the amendment to claim 7 can be found in claims 1 and 2, as originally filed.

Support for new claims 9-11 can be found in the specification at page 16, lines 17-25, as originally filed.

Support for new claims 12 and 13 can be found in the specification at page 17, lines 4-9, as originally filed.

Support for new claims 14 and 15 can be found in the specification at page 17, lines 10-13, as originally filed.

Support for new claim 16 can be found in claim 3, as originally filed.

No new matter has been added by these amendments.

Upon entry of this amendment, claims 1-16 will be active in this application. Claims 1-6 and 8 have been withdrawn, in view of a Restriction Requirement.